ABSTRACT

The present invention provides an annealed wafer manufacturing method using a heat treatment method causing no change in resistivity of a wafer surface even when a silicon wafer having boron deposited on a surface thereof from an environment is subjected to heat treatment in an insert gas atmosphere and enabling the heat treatment in an ordinary diffusion furnace not requiring a sealed structure for increasing airtightness nor any specific facility such as explosion-proof facility. The present invention also provides an annealed wafer in which a boron concentration in the vicinity of a surface thereof is constant and crystal defects are annihilated. In the annealed wafer manufacturing method, a silicon wafer having a natural oxide film formed on a surface thereof with boron deposited thereon from an environment is subjected to heat treatment in an atmosphere containing hydrogen gas to remove the deposited boron before the natural oxide film is removed, and then is subjected to heat treatment in an inert gas atmosphere.



162162



G00001